

# Anna Marzegalli

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

30  
papers

403  
citations

9  
h-index

19  
g-index

33  
ext. papers

500  
ext. citations

6.2  
avg. IF

3.16  
L-index

#	Paper	IF	Citations
30	Atomic-scale insights on the formation of ordered arrays of edge dislocations in Ge/Si(001) films via molecular dynamics simulations.. <i>Scientific Reports</i> , <b>2022</b> , 12, 3235	4.9	2
29	Nature and Shape of Stacking Faults in 3C-SiC by Molecular Dynamics Simulations. <i>Physica Status Solidi (B): Basic Research</i> , <b>2021</b> , 258, 2000598	1.3	0
28	Stress engineering of boron doped diamond thin films via micro-fabrication. <i>APL Materials</i> , <b>2021</b> , 9, 061109	1.3	0
27	Mechanism of stacking fault annihilation in 3C-SiC epitaxially grown on Si(001) by molecular dynamics simulations. <i>CrystEngComm</i> , <b>2021</b> , 23, 1566-1571	3.3	3
26	Extended defects in 3C-SiC: Stacking faults, threading partial dislocations, and inverted domain boundaries. <i>Acta Materialia</i> , <b>2021</b> , 213, 116915	8.4	11
25	New Approaches and Understandings in the Growth of Cubic Silicon Carbide. <i>Materials</i> , <b>2021</b> , 14,	3.5	6
24	The origin and nature of killer defects in 3C-SiC for power electronic applications by a multiscale atomistic approach. <i>Journal of Materials Chemistry C</i> , <b>2020</b> , 8, 8380-8392	7.1	9
23	In-plane selective area InSb/Al nanowire quantum networks. <i>Communications Physics</i> , <b>2020</b> , 3,	5.4	18
22	Molecular dynamics simulations of extended defects and their evolution in 3C-SiC by different potentials. <i>Modelling and Simulation in Materials Science and Engineering</i> , <b>2020</b> , 28, 015002	2	8
21	Structure and Stability of Partial Dislocation Complexes in 3C-SiC by Molecular Dynamics Simulations. <i>Materials</i> , <b>2019</b> , 12,	3.5	6
20	Temperature-Dependent Stability of Polytypes and Stacking Faults in SiC: Reconciling Theory and Experiments. <i>Physical Review Applied</i> , <b>2019</b> , 12,	4.3	17
19	Dynamics of crosshatch patterns in heteroepitaxy. <i>Physical Review B</i> , <b>2019</b> , 100,	3.3	6
18	Misfit-Dislocation Distributions in Heteroepitaxy: From Mesoscale Measurements to Individual Defects and Back. <i>Physical Review Applied</i> , <b>2018</b> , 10,	4.3	6
17	Lattice tilt and strain mapped by X-ray scanning nanodiffraction in compositionally graded SiGe/Si microcrystals. <i>Journal of Applied Crystallography</i> , <b>2018</b> , 51, 368-385	3.8	8
16	Solving the critical thermal bowing in 3C-SiC/Si(111) by a tilting Si pillar architecture. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 185703	2.5	5
15	Exceptional thermal strain reduction by a tilting pillar architecture: Suspended Ge layers on Si (001). <i>Materials and Design</i> , <b>2017</b> , 116, 144-151	8.1	9
14	Strain Engineering in Highly Mismatched SiGe/Si Heterostructures. <i>Materials Science in Semiconductor Processing</i> , <b>2017</b> , 70, 117-122	4.3	7

13	Structure, interface abruptness and strain relaxation in self-assisted grown InAs/GaAs nanowires. <i>Applied Surface Science</i> , <b>2017</b> , 395, 29-36	6.7	4
12	Photodetection in Hybrid Single-Layer Graphene/Fully Coherent Germanium Island Nanostructures Selectively Grown on Silicon Nanotip Patterns. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2016</b> , 8, 2017-26	9.5	25
11	Lattice bending in three-dimensional Ge microcrystals studied by X-ray nanodiffraction and modelling. <i>Journal of Applied Crystallography</i> , <b>2016</b> , 49, 976-986	3.8	5
10	3C-SiC Epitaxy on Deeply Patterned Si(111) Substrates. <i>Materials Science Forum</i> , <b>2016</b> , 858, 151-154	0.4	9
9	Burgers Vector Analysis of Vertical Dislocations in Ge Crystals by Large-Angle Convergent Beam Electron Diffraction. <i>Microscopy and Microanalysis</i> , <b>2015</b> , 21, 637-45	0.5	5
8	3D heteroepitaxy of mismatched semiconductors on silicon. <i>Thin Solid Films</i> , <b>2014</b> , 557, 42-49	2.2	16
7	Onset of vertical threading dislocations in Si <sub>1-x</sub> Ge <sub>x</sub> /Si (001) at a critical Ge concentration. <i>APL Materials</i> , <b>2013</b> , 1, 052109	5.7	13
6	Unexpected Dominance of Vertical Dislocations in High-Misfit Ge/Si(001) Films and Their Elimination by Deep Substrate Patterning (Adv. Mater. 32/2013). <i>Advanced Materials</i> , <b>2013</b> , 25, 4407-4407 <sup>24</sup>		2
5	Unexpected dominance of vertical dislocations in high-misfit ge/si(001) films and their elimination by deep substrate patterning. <i>Advanced Materials</i> , <b>2013</b> , 25, 4408-12	24	47
4	Perfect crystals grown from imperfect interfaces. <i>Scientific Reports</i> , <b>2013</b> , 3, 2276	4.9	28
3	Scaling hetero-epitaxy from layers to three-dimensional crystals. <i>Science</i> , <b>2012</b> , 335, 1330-4	33.3	125
2	Strained MOSFETs on ordered SiGe dots. <i>Solid-State Electronics</i> , <b>2011</b> , 65-66, 81-87	1.7	2
1	Strained MOSFETs on ordered SiGe dots <b>2010</b> ,		1